

DOCKET NO.: 209544US2

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
Youichi ISHIMURA, et al. ✓ : EXAMINER: TRAN, T.
SERIAL NO: 09/881,675 ✓ :
FILED: JUNE 18, 2001 ✓ : GROUP ART UNIT: 2811
FOR: FIELD-EFFECT SEMICONDUCTOR :
DEVICE

#12/B
Amst
NTE
J. McQuinn
4/3/03

TECHNOLOGY CENTER 2800

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AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated January 3, 2003, please amend the above-identified application as follows:

IN THE SPECIFICATION

Page 7, lines 2-17, please amend the paragraph to read as follows:

Fig. 1 is a vertical cross-sectional view that schematically shows the structure of an insulated gate bipolar transistor (abbreviated as IGBT hereafter) in accordance with a first embodiment of the present invention. In this IGBT 10, an n⁺-buffer layer 3 and an n- layer 2 are successively formed on a p⁺-collector layer 4 that consists of a p⁺-semiconductor substrate. Also, a p-base region 6 is formed as part of the upper surface of the n- layer 2. Further, high-density impurities of n type are selectively diffused to form n⁺-emitter regions 7 as part of the upper surface of the p-base region 6. The part of the surface region of the p-base region 6 which is located between the n⁺ layer 2 and the n⁺-emitter regions 7 forms a channel

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